

Appl. No. 09/855,820
Amdt. dated May 28, 2003
Reply to Office Action of January 29, 2003

PATENT

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1-23. (Canceled)

Claim 24. (Previously amended) A method for forming a carrier for a semiconductor die package, the method comprising:

- (a) providing a metal layer; and
(b) forming a plurality of bumps in the metal layer, wherein the formed bumps are capable of being electrically coupled to conductive regions of a circuit substrate, and wherein forming the plurality of bumps comprises stamping.

Claim 25. (Canceled)

Claim 26. (Original) A method for forming a semiconductor die package, the method comprising:

- (a) forming a carrier according to the method of claim 24; and
(b) attaching a semiconductor die to the metal layer after forming the plurality of bumps.

Claim 27. (Previously amended) The method of claim 26 wherein attaching comprises: attaching the semiconductor die to a die attach region of the carrier, and wherein the plurality of bumps is disposed around the semiconductor die.

Claim 29. (Previously added) The method of claim 24 wherein the bumps each have a conical shape.

Claim 30. (Previously added) The method of claim 24 wherein the metal layer comprises copper.

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Claim 31. (Previously added) The method of claim 24 wherein the bumps in the plurality of bumps are disposed in an array.

Claim 32. (Previously added) The method of claim 24 wherein the bumps in the plurality of bumps are arranged around a die attach region.

Claim 33. (Canceled)

C Claim 34. (Previously added) The method of claim 24 wherein the metal layer includes one or more sublayers of material on a base metal.

Claim 35. (Canceled)

Claim 36. (Previously added) The method of claim 24 wherein each bump has a conical angle of about 40 degrees or more.

Claim 37. (Previously added) The method of claim 24 wherein the plurality of bumps are formed simultaneously in the metal layer.